

L Number	Hits	Search Text	DB	Time stamp
3	8455	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:32
4	289	((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:38
5	30	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:40
6	0	chia-der-chang-hsin-chu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:41
7	0	hsin-chu-chia-der-chang.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:42
8	0	chia-der-chang.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:42
9	9	Yi-tung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:42
-	1	("0000424").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 13:47
-	49798	trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 13:47
-	389	trench and shore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 13:48
-	4	(trench and shore) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 14:29
-	1055	(438/692).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 12:44
-	14	((438/692).CCLS.) and (shore or (shore adj D))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 14:35

-	3	((438/692).CCLS.) and (shore or (shore adj D))) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 14:35
-	114633	(silicon adj (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 15:34
-	127	((silicon adj (substrate or wafer))) and (shore or (shore adj d))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 15:49
-	4	((silicon adj (substrate or wafer))) and (shore or (shore adj d)) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 15:49
-	1	("20020160546").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:07
-	14734	photo adj resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:15
-	3895	trench adj fill\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:09
-	53493	trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:09
-	22142	cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
-	23096	planariz\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
-	138	(photo adj resist) and (trench adj fill\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
-	61	((photo adj resist) and (trench adj fill\$2)) and cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
-	47	((photo adj resist) and (trench adj fill\$2)) and cmp) and planariz\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:10
-	266601	resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:15

-	14734	(photo adj resist) and resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:16
-	856	(trench adj fill\$2) and resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:16
-	351	cmp and ((trench adj fill\$2) and resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:16
-	254	(cmp and ((trench adj fill\$2) and resist)) and planariz\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/25 13:17
-	2	("5173439" "5719073").PN.	USPAT	2002/11/25 13:39
-	1	6107187.URPN.	USPAT	2002/11/25 13:39
-	2969	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.	USPAT; US-PGPUB	2003/11/05 13:53
-	200436	resist or (photo near2 resist)	USPAT; US-PGPUB	2003/07/09 13:35
-	838	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.) and (resist or (photo near2 resist))	USPAT; US-PGPUB	2003/07/09 13:34
-	24655	((resist or (photo near2 resist)) near (layer or film))	USPAT; US-PGPUB	2003/07/09 13:35
-	354	((resist or (photo near2 resist)) near (layer or film))) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.)	USPAT; US-PGPUB	2003/07/09 14:46
-	1	6117798.URPN.	USPAT	2003/07/09 14:38
-	6	("5607880" "5747381" "5783482" "5948700" "6030706" "6030892").PN.	USPAT	2003/07/09 14:38
-	1373	((438/424) or (438/427) or (438/443)).CCLS.	USPAT; US-PGPUB	2003/07/09 14:46
-	23154	(cmp or ((chemical adj mechanical) near2 polish))	USPAT; US-PGPUB	2003/10/23 16:31
-	717	((438/424) or (438/427) or (438/443)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB	2003/07/09 14:47
-	78	((438/424) or (438/427) or (438/443)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish)))) and (((resist or (photo near2 resist)) near (layer or film)))	USPAT; US-PGPUB	2003/07/09 15:59
-	71742	dish or dishing	USPAT; US-PGPUB	2003/07/09 15:59
-	443	(dish or dishing) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.)	USPAT; US-PGPUB	2003/07/09 16:05
-	0	6436833.URPN.	USPAT	2003/07/09 16:28
-	6	("5173439" "5721173" "5880007" "6001706" "6048775" "6107159").PN.	USPAT	2003/07/09 16:28
-	4	6171962.URPN.	USPAT	2003/07/09 16:45
-	5	("4613888" "5094972" "5298110" "5702977" "5817567").PN.	USPAT	2003/07/09 16:45
-	138	((438/424) or (438/427) or (438/443)).CCLS.) and ((cmp or ((chemical adj mechanical) near2 polish)))) and (dish or dishing)	USPAT; US-PGPUB	2003/07/09 16:52
-	3875	((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:34

-	50475	((rie or (reactive near2 ion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:30
-	32793	((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:10
-	1901	((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:31
-	156	((((438/780) or (438/781) or (438/782) or (438/692) or (438/633)).CCLS.) and ((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:31
-	7962	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:32
-	12015	(photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11
-	1202	((((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 16:48
-	129	((((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize)))) and ((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:09
-	1377	((((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:05
-	129	((((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish)))) and ((photoresist or resist) and (cmp or (chemical adj mechanical adj planarize)))) and (((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:05
-	4048	((cmp or ((chemical adj mechanical) near2 polish))) same (photoresist or resist) and (cmp or (chemical adj mechanical adj planarize))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11
-	4143	((cmp or ((chemical adj mechanical) near2 polish))) same (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11

-	419832	(photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:11
-	4143	((cmp or ((chemical adj mechanical) near2 polish))) same ((photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:12
-	1296	((cmp or ((chemical adj mechanical) near2 polish))) with ((photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:12
-	451	((cmp or ((chemical adj mechanical) near2 polish))) with ((photoresist or resist)) and ((rie or (reactive near2 ion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:12
-	55	((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.) and (((cmp or ((chemical adj mechanical) near2 polish))) with ((photoresist or resist)) and ((rie or (reactive near2 ion))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:15
-	624	((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))) same ((photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:17
-	42	((rie or (reactive near2 ion))) same ((cmp or ((chemical adj mechanical) near2 polish))) same ((photoresist or resist)) and ((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:44
-	244	((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/15 22:37
-	28	((cmp or ((chemical adj mechanical) near2 polish))) near2 ((photoresist or resist)) and ((438/780) or (438/781) or (438/782) or (438/692) or (438/633) or (438/693) or (438/697) or (438/698) or (438/699) or (438/700) or (438/702) or (438/703)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/23 17:44
-	1	("6613690").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/24 11:44
-	0	6613690.URPN.	USPAT	2003/10/24 11:44
-	8	("4385975" "5065273" "5077234" "5100823" "5723374" "5759262" "6130126" "6420226").PN.	USPAT	2003/10/24 11:44
-	2	6420226.URPN.	USPAT	2003/10/24 11:54
-	9	("5468979" "5805494" "5972759" "6013547" "6080638" "6130470" "6150686" "6174764" "6340623").PN.	USPAT	2003/10/24 11:54
-	7620	((438/780) or (438/781) or (438/782) or (438/692) or (438/626) or (438/631) or (438/633) or (438/693) or (438/725) or (438/697) or (438/699) or (438/760)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:57

-	39447	cmp or (chemical adj mechanical adj (polishing or planarizing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:58
-	421221	resist or photoresist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:59
-	19	((((438/780) or (438/781) or (438/782) or (438/692) or (438/626) or (438/631) or (438/633) or (438/693) or (438/725) or (438/697) or (438/699) or (438/760)).CCLS.) and ((cmp or (chemical adj mechanical adj (polishing or planarizing))) near (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:59
-	157	(cmp or (chemical adj mechanical adj (polishing or planarizing))) near (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25
-	1420928	remove	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25
-	8268	remove near (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25
-	17	(remove near (resist or photoresist)) with (cmp or (chemical adj mechanical adj (polishing or planarizing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:25